

5 A High Voltage Schottky Barrier Rectifier

#### DESCRIPTION

This UPS5100e3 in the Powermite3<sup>®</sup> package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3<sup>®</sup> package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

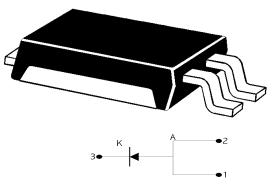
#### ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED) Symbol Unit Rating Value Peak Repetitive Reverse Voltage V<sub>RRM</sub> Working Peak Reverse Voltage 100 V VRWM DC Blocking Voltage $V_R$ **RMS Reverse Voltage** 70 V V<sub>R(RMS)</sub>

#### Average Rectified Output Current 5 А $I_0$ Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed 100 А I<sub>FSM</sub> on Rated Load@ T<sub>c</sub> =90 °C Storage Temperature T<sub>STG</sub> -55 to +150 °C °С Junction Temperature $T_{\rm J}$ -55 to +125

## THERMAL CHARACTERISTICS

Thermal Resistance			
Junction-to-Case (bottom)	R <sub>eJC</sub>	2.5	°C/ Watt
Junction to Ambient (1)	R <sub>θJA</sub>	65	°C/ Watt
1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print			

#### Powermite 3<sup>™</sup>



## **KEY FEATURES**

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
  Guard-ring-die construction for transient
- Guard-ring-die construction for transient protection
   Efficient heat noth with Integral leaking
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

#### APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I<sub>RM</sub>
- Small foot print 190 X 260 mils (1:1 Actual size) See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: \$5100•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel

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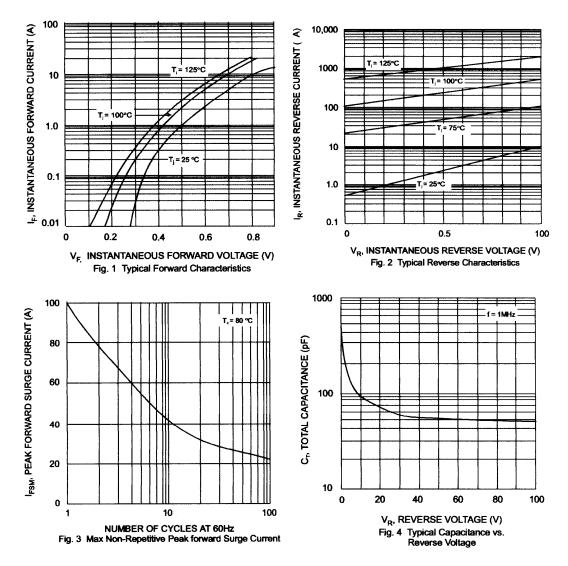
**UPS5100e3** 



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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)						
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
Forward Voltage (Note 1)	VF	$ \begin{split} I_F &= 5 \; A \;, \; T_L = 25 \; ^{\circ}C \\ I_F &= 5 \; A \;, \; T_L = 125 \; ^{\circ}C \\ I_F &= 10 \; A \;, \; T_L = 25 \; ^{\circ}C \end{split} $		0.75 0.58 0.84	0.81 0.64 0.90	v
Reverse Break Down Voltage (Note 1)	V <sub>BR</sub>	I <sub>F</sub> = 10 A , T <sub>L</sub> = 125 °C I <sub>R</sub> = 0.2 mA	100	0.67	0.73	V
Reverse Current (Note1)	I <sub>R</sub>	V <sub>R</sub> = 100V, T <sub>j</sub> = 25°C V <sub>R</sub> = 100V, T <sub>j</sub> = 125 °C		15 10	200 20	μA mA
Capacitance	CT	V <sub>R</sub> = 4 V; f = 1 MH <sub>Z</sub>		150		pF

Note: 1 Short duration test pulse used to minimize self – heating effect.



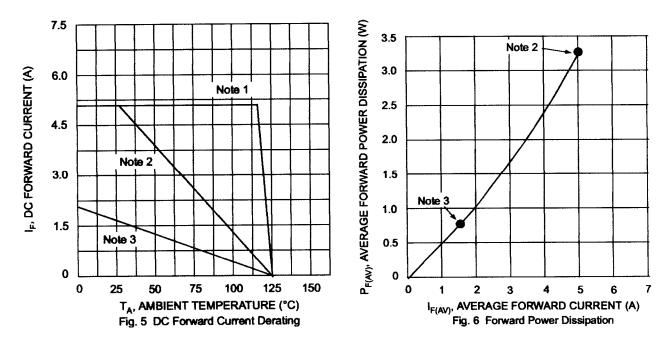
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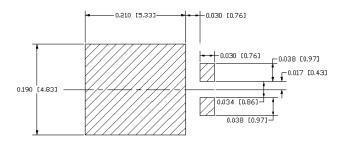


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- Notes: 1.  $T_A = T_{SOLDERING POINT}$ ,  $R_{\Theta JS} = 2.5C/W$ ,  $R_{\Theta SA} = 0^{\circ}C/W$ .
  - Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R<sub>OJA</sub> in range of 20-35°C/W.
    - 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout  $R_{\Theta JA}$  in range of 65°C/W. See mounting pad below.

## MOUNTING PAD LAYOUT



Mounting Pad Dimensions: inches [mm]

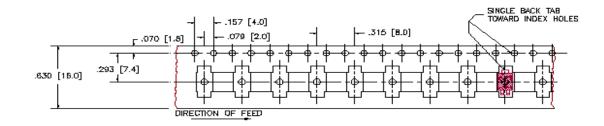
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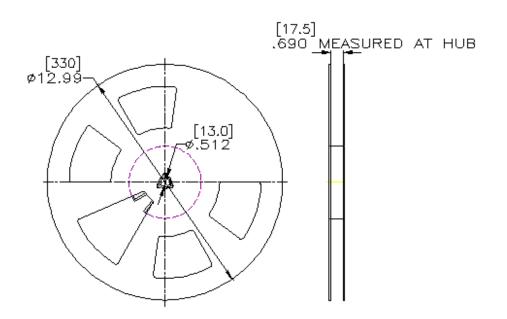


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## TAPE & REEL



## 13 INCH REEL



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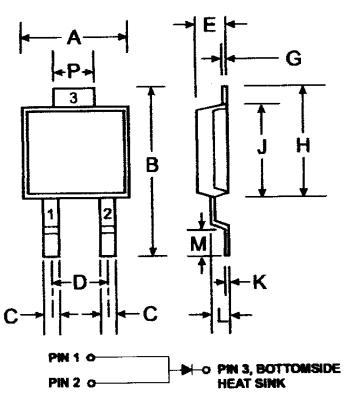
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## PACKAGE DIMENSIONS



Note:	Pins 1 & 2 must be electrically
	connected at the printed circuit board.

POWERMITE®3				
Dim	Min	Max		
•	4.03	4.09		
B	6.40	6.61		
С	.889 NOM			
D	1.83 NOM			
E	1.10	1.14		
G	.178 NOM			
Н	5.01	5.17		
J	4.37	4.43		
К	.178 NOM			
L	.71	.77		
M	.36	.46		
Р	1.73	1.83		
All Dimensions in mm				

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